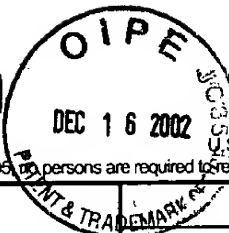


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Sheet 2 of 2

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|                        |                   |
|------------------------|-------------------|
| Application Number     | 09/747,779        |
| Filing Date            | December 22, 2000 |
| First Named Inventor   | Kim, Hong Koo     |
| Group Art Unit         | 1765              |
| Examiner Name          | Unassigned        |
| Attorney Docket Number | 000939-073311US   |

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## OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

| Examiner Initials * | Cite No. <sup>1</sup> | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.         | T <sup>2</sup> |
|---------------------|-----------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------|
| LDP                 | AA                    | BASIT et al., "Growth of highly oriented Pb(Zr, Ti)O <sub>3</sub> films on MgO-buffered oxidized Si substrates and its application to ferroelectric nonvolatile memory field-effect transistors," <u>Applied Physics Letters</u> , 73(26):3941-3943 (1998).             |                |
| LDP                 | AB                    | BASIT et al., "Temperature dependence of lead loss in r.f. magnetron sputtering of a stoichiometric Pb(Zr, Ti)O <sub>3</sub> target," <u>Thin Solid Films</u> , 302:155-161 (1997).                                                                                     |                |
| LDP                 | AC                    | BASIT et al., "Crystallization of Pb(Zr, Ti)O <sub>3</sub> films prepared by rf magnetron sputtering with a stoichiometric oxide target," <u>J. Vac. Sci. Technol.</u> , A 13(4):2214-2220 (1995).                                                                      |                |
| LDP                 | AD                    | BUHAY et al., "Pulsed laser deposition and ferroelectric characterization of bismuth titanate films," <u>Appl. Phys. Lett.</u> , 58(14):1470-1472 (1991).                                                                                                               |                |
| LDP                 | AE                    | DAX, M., eds., "The Non-Volatile Memory Challenge," <u>Semiconductor International</u> , September 1997, pages 84-92.                                                                                                                                                   |                |
| LDP                 | AF                    | HAN et al., "SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>7</sub> memory capacitor on Si with a silicon nitride buffer," <u>Applied Physics Letters</u> , 72(10):1185-1186 (1998).                                                                                          |                |
| LDP                 | AG                    | HIRAI et al., "Formation of Metal / Ferroelectric / Insulator / Semiconductor Structure with a CeO <sub>2</sub> Buffer Layer," <u>Jpn. J. Appl. Phys.</u> , 33(9B)pt. 1: 5219-5222 (1994).                                                                              |                |
| LDP                 | AH                    | KIM et al., "Memory window of Pt-Bi <sub>2</sub> Ta <sub>2</sub> O <sub>7</sub> /CeO <sub>2</sub> /Si structure for metal ferroelectric insulator semiconductor field effect transistor," <u>Appl. Phys. Lett.</u> , 71(24):3507-3509 (1997).                           |                |
| LDP                 | AI                    | MILLER et al., "Physics of the ferroelectric nonvolatile memory field effect transistor," <u>J. Appl. Phys.</u> , 72(12):5999-6010 (1992).                                                                                                                              |                |
| LDP                 | AJ                    | NASHIMOTO et al., "Epitaxial growth of MgO on GaAs(001) for growing epitaxial BaTiO <sub>3</sub> thin films by pulsed laser deposition," <u>Appl. Phys. Lett.</u> , 60(10):1199-1201 (1992).                                                                            |                |
| LDP                 | AK                    | ROST et al., "Ferroelectric switching of a field-effect transistor with a lithium niobate gate insulator," <u>Appl. Phys. Lett.</u> , 59(27):3654-3656 (1991).                                                                                                          |                |
| LDP                 | AL                    | SINHARROY et al., "Growth and characterization of ferroelectric BaMgF <sub>4</sub> films," <u>J. Vac. Sci. Technol.</u> , A9(3):409-413 (1991).                                                                                                                         |                |
| LDP                 | AM                    | TOKUMITSU et al., "Nonvolatile Memory Operations of Metal-Ferroelectric-Insulator-Semiconductor (MFIS) FET's Using PLZT/STO/Si(100) Structures," <u>IEEE Electric Device Letters</u> , 18(4):160-162 (1997).                                                            |                |
| LDP                 | AN                    | WANG et al., "Deposition of in-plane textured MgO on amorphous Si <sub>3</sub> N <sub>4</sub> substrates ion-beam-assisted deposition and comparisons with ion-beam-assisted deposited yttria-stabilized-zirconia," <u>Appl. Phys. Lett.</u> , 71(20):2955-2957 (1997). |                |
| LDP                 | AO                    | WU, Shu-Yau, "A New Ferroelectric Memory Device, Metal-Ferroelectric-Semiconductor Transistor," <u>IEEE Transactions on Electron Devices</u> , ED-21(8):499-504 (1974).                                                                                                 |                |

Examiner Signature

*[Signature]*

Date Considered

2/20/2003

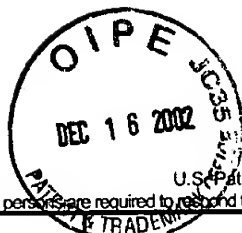
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Sheet **1** of **2**

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| Examiner Name          | Unassigned        |
| Attorney Docket Number | 000939-073311US   |

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## **U.S. PATENT DOCUMENTS**

| Examiner<br>Initials * | Cite<br>No. <sup>1</sup> | U.S. Patent Document |                                      | Name of Patentee or Applicant<br>of Cited Document | Date of Publication of<br>Cited Document<br>MM-DD-YYYY | Pages, Columns, Lines,<br>Where Relevant<br>Passages or Relevant<br>Figures Appear |
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| Examiner<br>Initials * | Cite<br>No. <sup>1</sup> | Foreign Patent Document |                     |                                      | Name of Patentee<br>or Applicant of<br>Cited Document | Date of Publication of<br>Cited Document<br>MM-DD-YYYY | Pages, Columns, Lines,<br>Where Relevant<br>Passages or Relevant<br>Figures Appear | T <sup>6</sup> |
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